

Supplement to:

Deep brain stimulation alleviates parkinsonian bradykinesia by regularizing pallidal activity

Alan D. Dorval, Alexis M. Kuncel, Merrill J. Birdno, Dennis A. Turner and Warren M. Grill

The main manuscript details simulations with the version of a computational model of the basal ganglia thalamic circuit (Terman et al., 2002; Rubin and Terman, 2004) described here. The XPP implementation will be provided upon request.

Briefly, sixteen point neurons in each of the four regions – subthalamic nucleus (STN), globus pallidus externus (GPe), globus pallidus internus (GPi) and pallidal receiving thalamic cells (TC) – comprise the model. Each neuron is represented by ordinary differential equations (ODEs) describing the membrane potential and ionic channel conductance gates as described below. All parameter values are listed in Tables 1-4.

Basal Ganglia Neurons. Neurons in basal ganglia (i.e. STN, GPe and GPi) were described by five ODEs.

$$\begin{aligned} c_m \frac{dV}{dt} &= I_{app} - I_{Na} - I_K - I_{Ca} - I_T - I_{ahp} - I_L - I_{syn} & \frac{dc}{dt} &= -\epsilon(I_{Ca} + I_T + k_{Ca}c) \\ \frac{dn}{dt} &= \frac{\phi_n}{\tau_n}(n_\infty - n) & \frac{dh}{dt} &= \frac{\phi_h}{\tau_h}(h_\infty - h) & \frac{dr}{dt} &= \frac{\phi_r}{\tau_r}(r_\infty - r) \end{aligned}$$

Applied (I_{app}) and synaptic (I_{syn}) currents are discussed in the main text, *NEURONAL INPUTS*. Ionic currents were:

$$\begin{aligned} I_{Na} &= G_{Na} m_\infty^3 h (V - V_{Na}) & I_K &= G_K n^4 (V - V_K) & I_{Ca} &= G_{Ca} s_\infty^2 (V - V_{Ca}) \\ I_T &= G_T a_\infty^3 b_r (V - V_{Ca}) & I_{ahp} &= G_{ahp} \frac{c}{c + k_{ahp}} (V - V_K) & I_L &= G_L (V - V_L) \end{aligned}$$

Gating steady states and time constants were $x_\infty = (1 + e^{(V - \theta_x)/\sigma_x})^{-1}$ and $\tau_x = \tau_{x0} + \tau_{xl}/(1 + e^{(V - \psi_x)/\xi_x})$. For pallidal neurons $b_r = r$, while for STN neurons $b_r = ((1 - e^{-14.29r})/(1.028 + e^{-14.29r}))^2$.

Thalamic Neurons. Thalamic cells were described by three ODEs:

$$c_m \frac{dV}{dt} = I_{smc} - I_{Na} - I_K - I_T - I_L - I_{syn} \quad \frac{dh}{dt} = \frac{1}{\tau_h}(h_\infty - h) \quad \frac{dr}{dt} = \frac{1}{\tau_r}(r_\infty - r)$$

where the current from sensory motor cortex (I_{smc}) was a time varying input signal. The ionic currents were:

$$\begin{aligned} I_{Na} &= G_{Na} m_\infty^3 h (V - V_{Na}) & I_K &= G_K n^4 (V - V_K) \\ I_T &= G_T p_\infty^2 r (V - V_{Ca}) & I_L &= G_L (V - V_L) \end{aligned}$$

where the steady state gating variables were described by $x_\infty = (1 + e^{(V - \theta_x)/\sigma_x})^{-1}$, with time constants

$\tau_h = (.128 e^{(V+46)/l-18} + \frac{4}{1 + e^{(V+23)/l-5}})^{-1}$ and $\tau_r = 28 + e^{(V+25)/l-10.5}$. The potassium activation gate was defined in terms of the sodium inactivation gate: $n = \frac{3}{4}(1-h)$.

References

- Rubin JE, Terman D. High frequency stimulation of the subthalamic nucleus eliminates pathological thalamic rhythmicity in a computational model. *J Comput Neurosci* 16: 211-235, 2004.
- Terman D, Rubin JE, Yew AC, Wilson CJ. Activity patterns in a model for the subthalamopallidal network of the basal ganglia. *J. Neurosci* 22: 2963-2976, 2002.

Tables

Table 1. Current Parameters

		STN	GPe	GPi	TC
c_m	pF/ μm^2	1	1	1	1
V_L	mV	-60	-55	-55	-70
V_{Na}	mV	55	55	55	50
V_K	mV	-80	-80	-80	-90
V_{Ca}	mV	140	120	120	0
G_L	nS/ μm^2	2.25	0.10	0.10	0.05
G_{Na}	nS/ μm^2	37.5	120	120	3
G_K	nS/ μm^2	45	30	30	5
G_T	nS/ μm^2	0.5	0.5	0.5	5
G_{Ca}	nS/ μm^2	0.50	0.15	0.15	
G_{ahp}	nS/ μm^2	9	30	30	
ε	$\mu\text{m}^2/\text{zC}$	37.5	100	100	
k_{Ca}	pA/ μm^2	22.5	15	15	
k_{ahp}	\emptyset	15	30	30	

Table 3. Synaptic Parameters

<i>synapses from</i>		STN	GPe	GPi
Vsyn	mV	0	-85	-85
G_{syn}	nS/ μm^2	0.15	0.50	0.04
α	ms^{-1}	3	2	2
β	ms^{-1}	0.01	0.04	0.04
θ_z	mV	-9	-37	-37
σ_z	mV	-8	-2	-2

Table 2a. Advanced Gate Parameters

	θ	σ	φ	τ_0	τ_1	ψ	ξ
	mV	mV	\emptyset	ms	ms	mV	mV
STN							
h	-39	3.1	0.75	1.0	500	-57	3.0
n	-32	-8.0	0.75	1.0	100	-80	26
r	-67	2.0	0.50	7.1	17.5	68	2.2
GPe & GPi							
h	-58	12	.05	.05	.27	-40	12
n	-50	-14	.10	.05	.27	-40	12
r	-70	2	1	30	0	0	1

Table 2b. Simple Gate Parameters

	θ	σ		θ	σ		θ	σ
	mV	mV		mV	mV		mV	mV
STN								
m	-30	-15		m	-37	-10		
s	-39	-8.0		s	-35	-2		
a	-63	-7.8		a	-57	-2		
GPe & GPi								
m	-37	-10		r	-84	4.0		
s	-35	-2		m	-37	-7.0		
a	-57	-2		p	-60	-6.2		
TC								

Table 4. Tonic Applied Currents

	STN	GPe		GPi		
		CTRL	w/PD	CTRL	w/PD	
I_{app}	pA/ μm^2	25	20±2	5±2	21	12